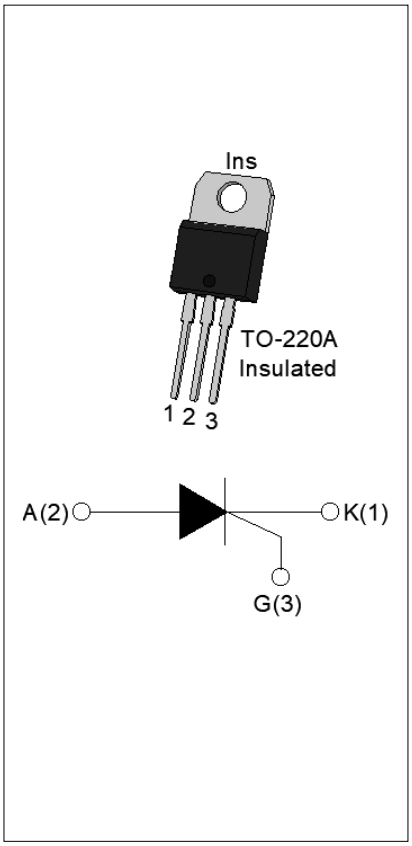
JCT151A-800R 12A SCR

Rev.A.1.1

D

With high ability to withstand the shock loading of large current, JCT151A-800R of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. From all three terminals to external heatsink, JCT151A-800R provides a rated insulation voltage of 2500 $V_{RMS,}$ complying with UL standards (File ref: E252906).
Package TO-220A is RoHS compliant.



M

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	800	V
I_{GT}	≤15	mA

E M R

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage (T_j=25)	V_{DRM}	800	V
Repetitive peak reverse voltage (T_j=25)	V_{RRM}	800	V
Average on-state current (T_C 95)	$I_{T(AV)}$	7.5	A
RMS on-state current (T_C 95)	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current (t_p=10ms, T_j=25)	I_{TSM}	120	A
Non repetitive surge peak on-state current (t_p=8.3ms, T_j=25)		132	
I^2t value for fusing (t_p=10ms , T_j=25)	I^2t	72	A^2s
Critical rate of rise of on-state current (I_G=2× I_{GT}, f=100Hz , T_j=125)	dI/dt	100	A/μs

S

J CT 151 A -800R

- J: JieJie Microelectronics Co., Ltd.
- CT: SCRs
- 151: IT(RMS):12A
- A: A:TO-220A(Ins)
- 800R: 800R:VDRM /VRRM 800V

S

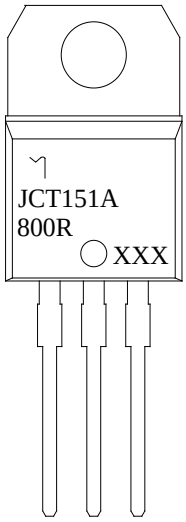
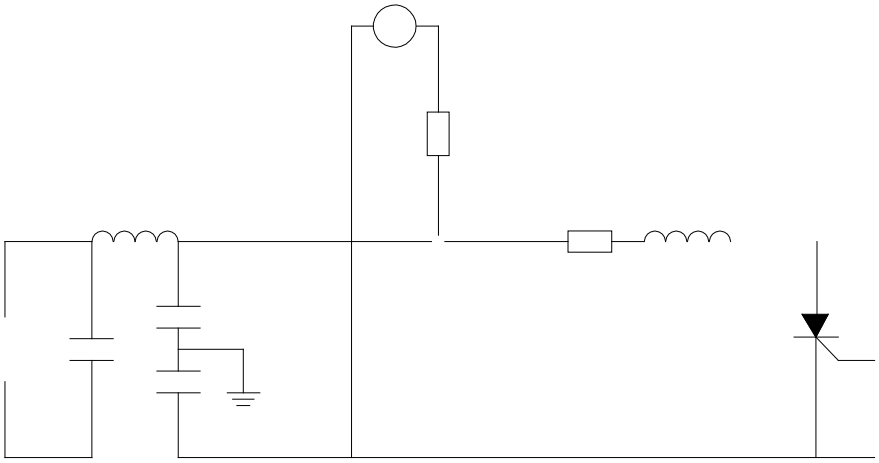


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



Order code	Voltage V_{DRM}/V_{RRM} (V)		Package	

Information furnished in this document is believed to be accurate and reliable.
However, Jiangsu JieJie Microelectronics Co., Ltd.